R18

Q.P. Code: 18EC0431

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(AUTONOMOUS)																		
			B.Tec	h IV	Year l	Sem		_			tions	Febru	uary	-2022				
					T1 .			LSI DI										
	Cina (a. 2 harma		(Electi	ronics	and C	ommı	ınıcatı	on En	ginee	ring)		M	ov Ma	1-~.	(0	
1	IIIIE	e: 3 hours						DAI	DT A					IVI	ax. Ma	rks:	60	
		(Answer all the Questions $5 \times 2 = 10 \text{ Marks}$)																
1	a	D 0										1	_1	2M				
	b													_2	2M			
	c													I	_1	2M		
	d		What are the high-density memory elements? Explain in brief.												_2	2M		
	e What is the need of Testing?														I	_1	2M	
PART-B (Angwer all Five Units 5 v 10 = 50 Merks)																		
(Answer all Five Units 5 x $10 = 50$ Marks)																		
2		UNIT-I Illustrate about basic MOS transistors										T	.2	4M				
4	a b							mnle	BiCN	AOS	inver	ter ar	nd .	evnlain			6M	
	D	Show the circuit diagram of a simple BiCMOS inverter and explain its operation.									165	11	UIVI					
								(OR									
3	Illu	istrate the s	teps in	nvolve	d in n	MOS	fabrica	ation p	roces	s with	neat s	sketche	es.		L	_2	10M	
								AND DESCRIPTION OF THE PERSON	IT-II									
4	a	Explain th	-					_								.2	5M	
	b	Construct	the sti	ick dia	gram	of a 2	-input			ND ga	ite.				I	_3	5M	
5	0	OR Construct stick diagram for $V = (AP + CP)$ in NMOS design style												т	.3	5M		
3	a	Construct stick diagram for $Y = (\overline{AB + CD})$ in NMOS design style. Construct the layout diagram for 2-input CMOS NOR gate.										13 13	5M					
	b Construct the layout diagram for 2-input CMOS NOR gate. UNIT-III												13	SIVI				
6	a	Sketch 2 x	t 1 mu	x usin	o tran	smissi	on gat	Mary Mary Company	1 -111						T	.3	5M	
v	b	What is ps							exam	ple						1	5M	
								()R									
7		plain the fo		_											I	ـ2	10M	
	(1)	Floor planr	ning	(11) Pla	aceme	nt (11	ı) Rou	The real Property lies and the least lies and the lies and the least lies and the lies and the least lies and the lies and t										
0	C		1.	! 41			• 4	ALC: UNKNOWN	T-IV							1	1034	
8	Co	nstruct and	expia	in the	rippie	coun	er wit			nes.					1	.1	10M	
9	Explain in detail about 6-transistor Static memory cell. UNIT-V												I	.2	10M			
															T OTIE			
10	a												are I	.2	5M			
		indistingui	ishable	Э.														
	b	What is Fl	PGA?	Draw	and e	xplain	basic			FPGA	A .				I	.1	5M	
11		Diag 1	41	. P	la		1 1.)R							1	73. 7	
11	_	Discuss at								10000						1	5M	
	b	Explain C	mp Le	vei 16	esi tec	ımıqu	es and	ns me	onoac	rogy.					L	. 2	5M	